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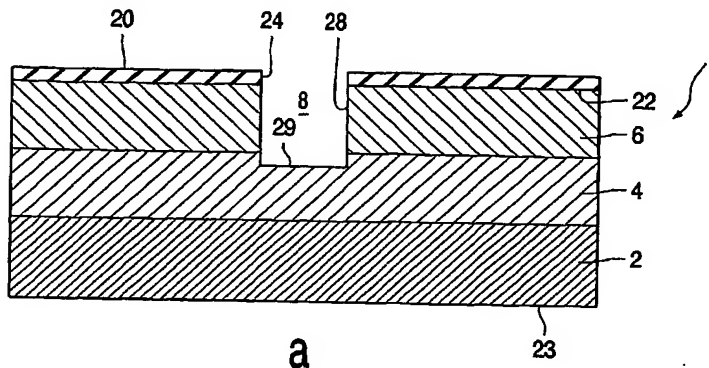
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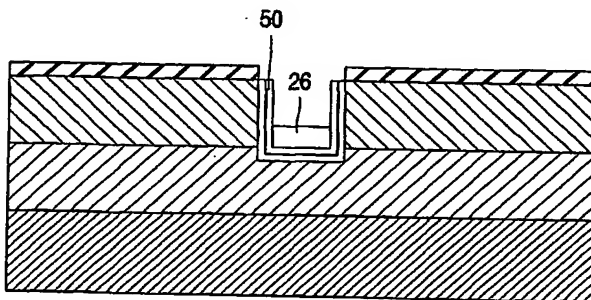
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(54) Title: METHOD OF MANUFACTURING A TRENCH-GATE SEMICONDUCTOR DEVICE



(57) Abstract: A method of making a trench MOSFET includes forming a nitride liner 50 on the sidewalls 28 of a trench and a plug of doped polysilicon 26 at the bottom of a trench. The plug of polysilicon 26 may then be oxidised to form a thick oxide plug 30 at the bottom of the trench whilst the nitride liner 50 protects the sidewalls 28 from oxidation. This forms a thick oxide plug at the bottom of the trench thereby reducing capacitance between gate and drain.



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